



Substitute for form 1449A/PTO

~~INFORMATION DISCLOSURE
STATEMENT BY APPLICANT~~

(use as many sheets as necessary)

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<i>Complete If Known</i>	
Application Number	10/816,282
Filing Date	March 31, 2004
First Named Inventor	Peter L.D. Chang
Art Unit	2818
Examiner Name	Ho, Tu Tu V.
Attorney Docket Number	42P18252

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Signature	TU-TU HO	Date Considered	Dec-2005
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**Applicant's unique citation designation number (optional). *See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. *Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). *For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. *Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. *Applicant is to place a check mark here if English language Translation is attached.*

Based on PTO/SB/DBA (03-03) as modified by Blakely, Schokoff, Taylor & Zafman (wtr) 08/11/2003.

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Sheet	2	of	2		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No'	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T?
<i>TP</i>		Nowak EJ, et al., "Turning Silicon On Its Edge - Overcoming silicon scaling barriers with double-gate and FinFET technology," IEEE Circuits and Devices Mag. vol. 20, no. 1, January 2004, pgs 20-31.	
<i>TP</i>		Fried, DM, et al. "Improved Independent Gate N-Type FinFET Fabrication and Characterization," IEEE Electron Device Letters, vol. 24, no. 9, September 2003, pages 592-594.	
<i>TP</i>		Fried, DM, et al. "A Fin-Type Independent-Double-Gate NFET," Device Research Conference, 2003 June, IEEE, 23 June 2003, pages 45-46.	
<i>TH</i>		PCT Search Report, Int'l application no. PCT/US2005/010164, mailed 07-27-2005, 5 pgs.	

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